

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (π-MOSIV)

2SK3742

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 2.2 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 3.5 S$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu A$ ($V_{DS} = 720 V$)
- Enhancement model: $V_{th} = 4.0 \sim 5.0 V$ ($V_{DS} = 10 V$, $I_D = 1 mA$)

Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	900	V
Drain-gate voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	900	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	5	A
	Pulse ($t = 1 ms$) (Note 1)	I_{DP}	15	
Drain power dissipation ($T_c = 25^\circ C$)		P_D	45	W
Single pulse avalanche energy (Note 2)		E_{AS}	595	mJ
Avalanche current		I_{AR}	5	A
Repetitive avalanche energy (Note 3)		E_{AR}	4.5	mJ
Channel temperature		T_{ch}	150	$^\circ C$
Storage temperature range		T_{stg}	-55~150	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	2.78	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

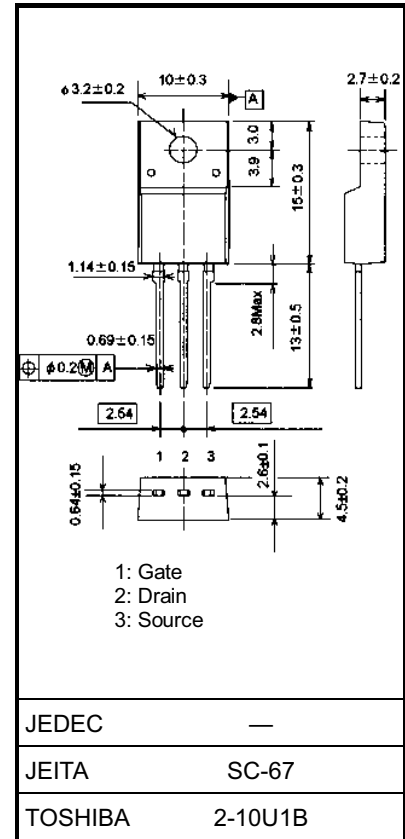
Note 1: Ensure that the channel temperature does not exceed $150^\circ C$ during use of the device.

Note 2: $V_{DD} = 90 V$, $T_{ch} = 25^\circ C$ (initial), $L = 43.6 mH$, $I_{AR} = 5.0 A$, $R_G = 25 \Omega$

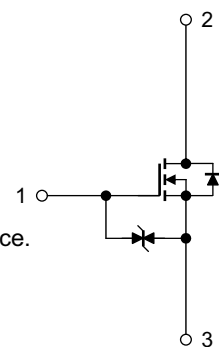
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

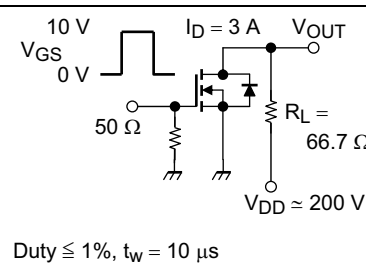
Unit: mm



Weight: 1.7 g (typ.)



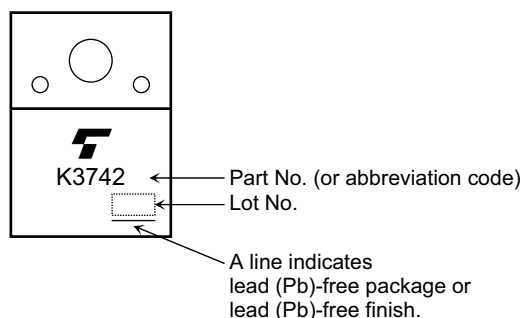
Electrical Characteristics (Ta = 25°C)

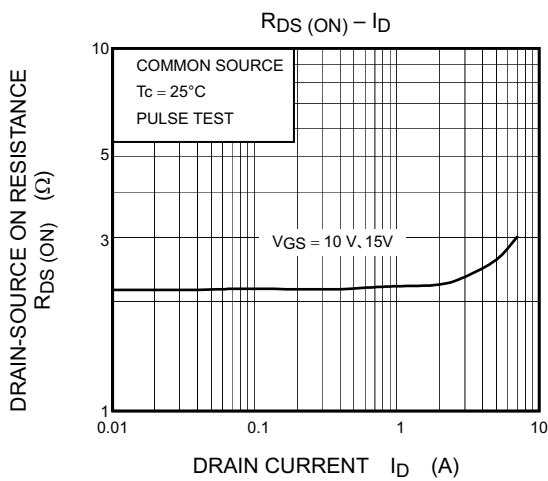
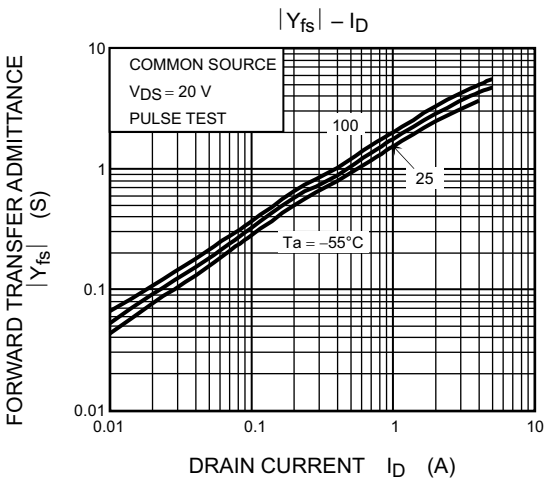
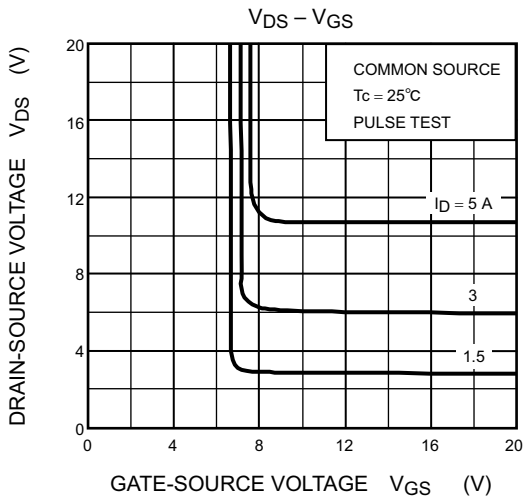
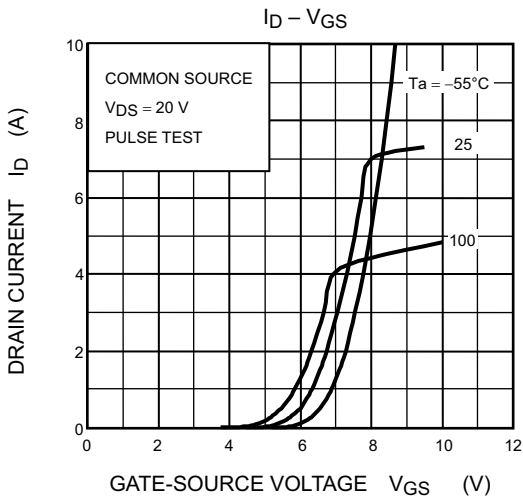
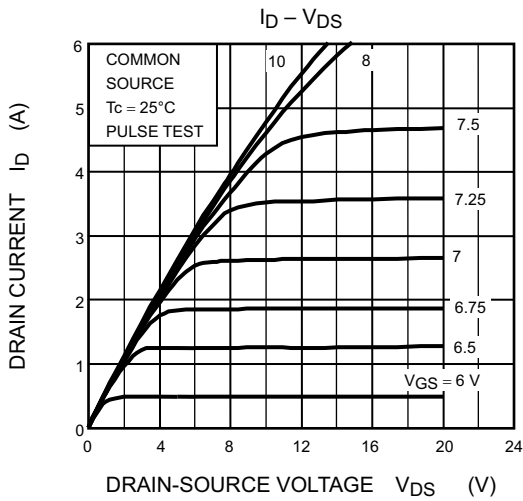
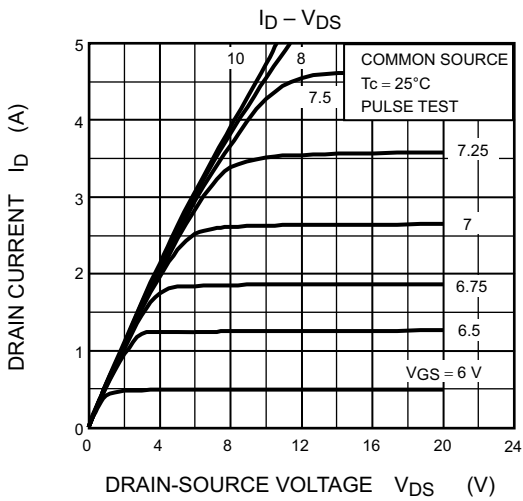
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Gate-source breakdown voltage		$V_{(BR) GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V
Drain cutoff current		I_{DSS}	$V_{DS} = 720 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR) DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	900	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	4.0	—	5.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$	—	2.2	2.5	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 20 \text{ V}, I_D = 3 \text{ A}$	1.5	3.5	—	S
Input capacitance		C_{iss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1150	—	pF
Reverse transfer capacitance		C_{rss}		—	20	—	
Output capacitance		C_{oss}		—	110	—	
Switching time	Rise time	t_r		—	100	—	ns
	Turn-on time	t_{on}		—	140	—	
	Fall time	t_f		—	40	—	
	Turn-off time	t_{off}		—	130	—	
Total gate charge		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$	—	25	—	nC
Gate-source charge		Q_{gs}		—	11	—	
Gate-drain charge		Q_{gd}		—	14	—	

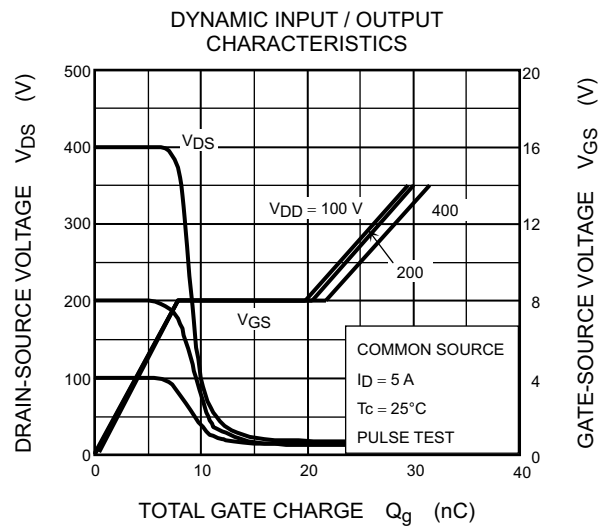
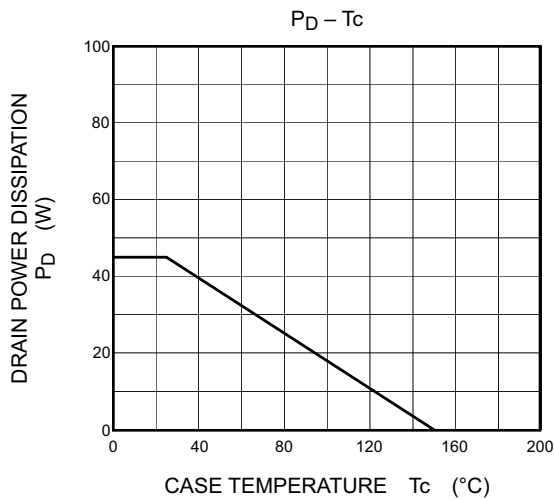
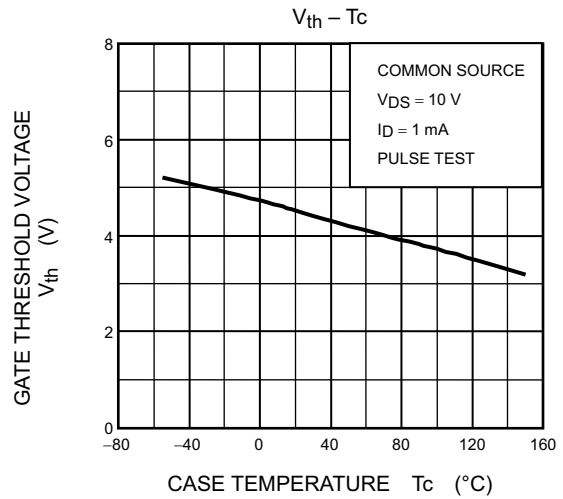
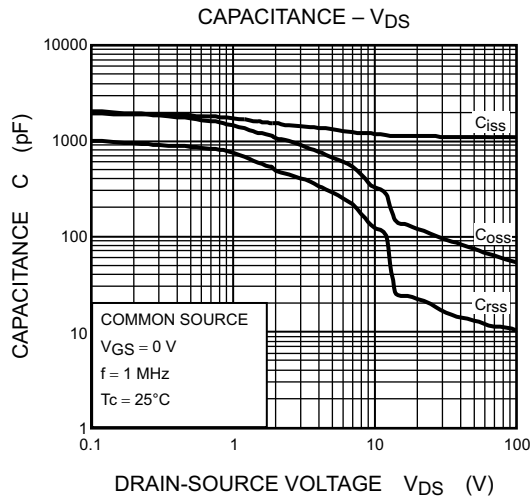
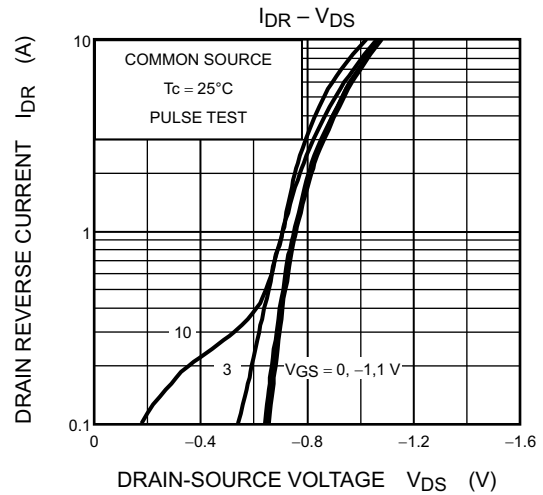
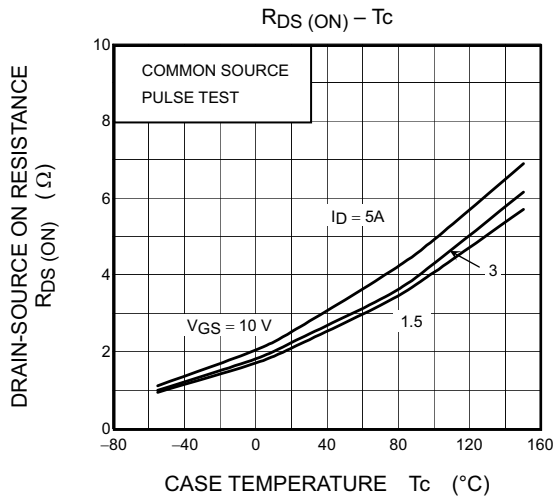
Source-Drain Ratings and Characteristics (Ta = 25°C)

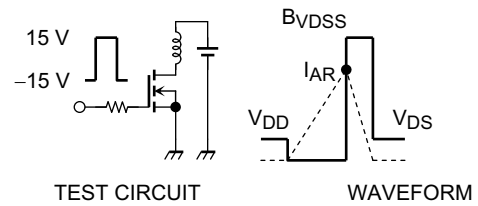
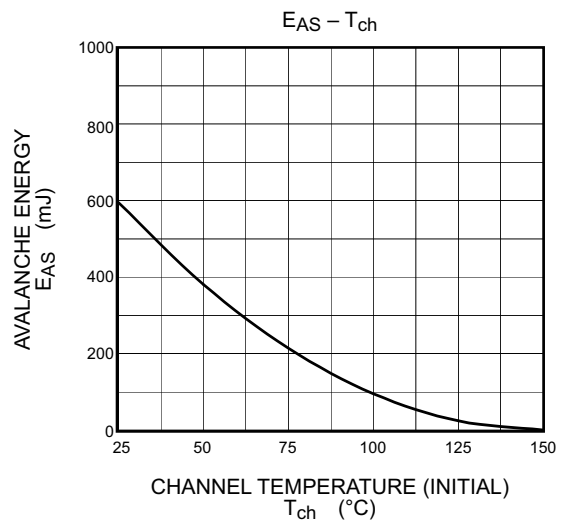
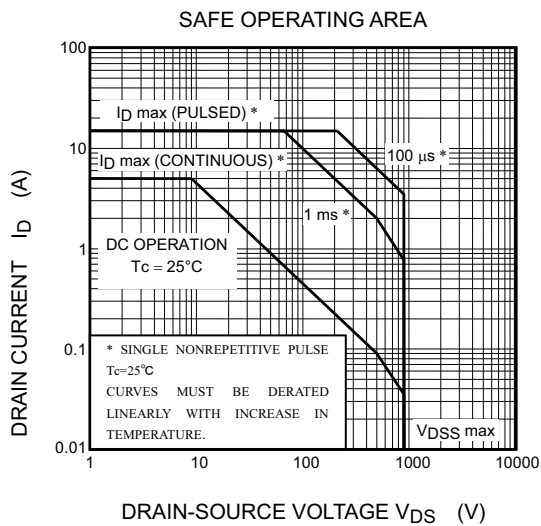
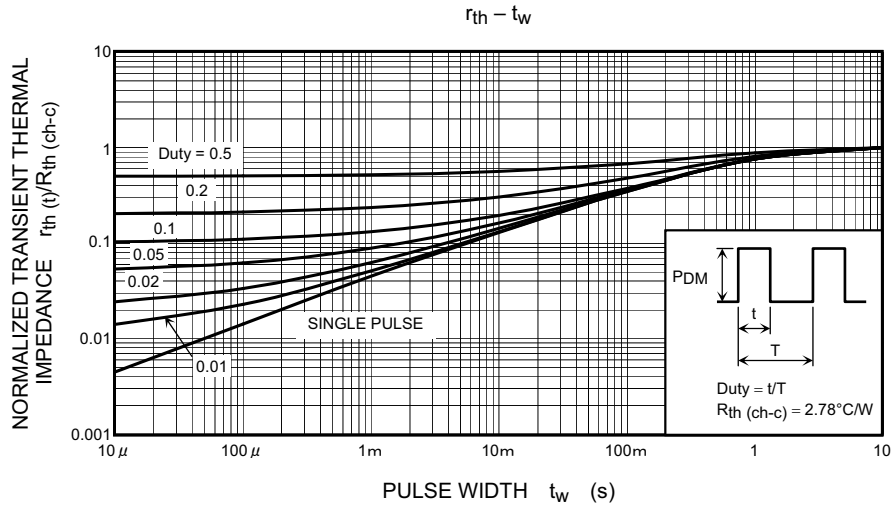
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	15	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V},$	—	900	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	5.4	—	μC

Marking









$$R_G = 25 \, \Omega$$

$$V_{DD} = 90 \, \text{V}, L = 43.6 \, \text{mH}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$